

BSS84W P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

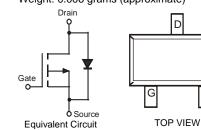
Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)





Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characterist	ic	Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	-50	V
Drain-Gate Voltage (Note 1)		V _{DGR}	-50	V
Gate-Source Voltage	Continuous	V _{GSS}	±20	V
Drain Current (Note 1)	Continuous	I _D	-130	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	Pd	200	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
				-15	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C
Zero Gate Voltage Drain Current	IDSS			-60	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C
				-100	nA	$V_{DS} = -25V, V_{GS} = 0V, T_{J} = 25^{\circ}C$
Gate-Body Leakage	I _{GSS}		_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	-1.6	-2.0	V	$V_{DS} = V_{GS}, I_D = -1mA$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	6	10	Ω	V _{GS} = -5V, I _D = -0.100A
Forward Transconductance	g fs	.05	_		S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS						·
Input Capacitance	Ciss	_	_	45	pF	
Output Capacitance	Coss	_	_	25	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	_	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}		10	_	ns	$V_{DD} = -30V, I_D = -0.27A,$
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns	$R_{GEN} = 50\Omega, V_{GS} = -10V$

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which Notes: can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. 3.

Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to 4. Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

5.

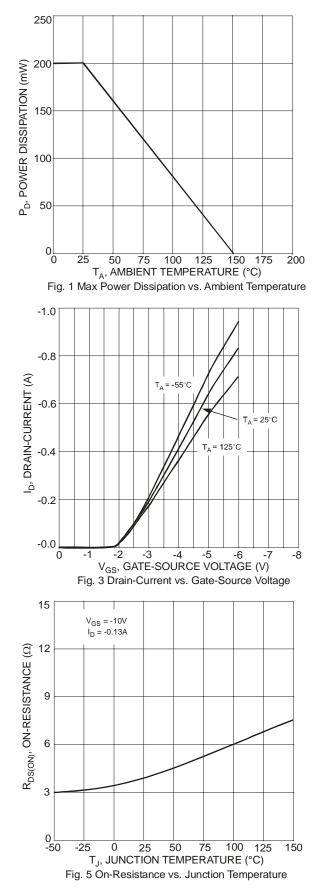
Short duration pulse test used to minimize self-heating effect.

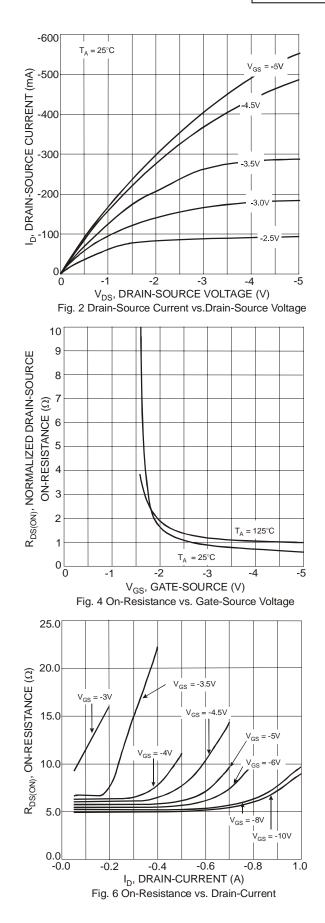


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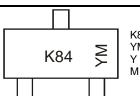


Ordering Information (Notes 4 and 6)

Part Number	Case	Packaging
BSS84W-7-F	SOT-323	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

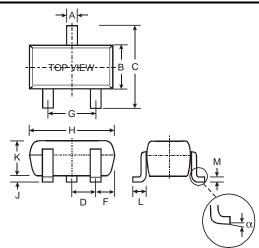


K84 = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

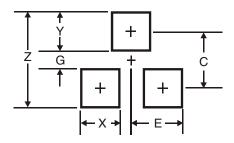
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	К	L	М	Ν	Р	R	S	Т	U	V	W	Х	Y	Z
Month	Jan	Fe	b I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D

Package Outline Dimensions



SOT-323							
Dim	Min	Max					
Α	0.25	0.40					
В	1.15	1.35					
С	2.00	2.20					
D	0.65 Nominal						
F	0.30	0.40					
G	1.20	1.40					
Н	1.80	2.20					
J	0.0	0.10					
K	0.90	1.00					
L	0.25	0.40					
М	0.10	0.18					
α	0°	8°					
All Di	mensions	in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
G	1.0
Х	0.7
Y	0.9
С	1.9
E	0.65

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